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ABSTRACT OF THE DISCLOSURE

[A method for making]

A circuit device that includes a first transistor having a first metal gate electrode overlying a first gate dielectric on a first area of a semiconductor substrate. The first gate electrode has a work function corresponding to the work function of one of P-type silicon and N-type silicon. The circuit device also includes a second transistor coupled to the first transistor. The second transistor has a second metal gate electrode over a second gate dielectric on a second area of the semiconductor substrate. The second gate metal gate electrode has a work function corresponding to the work function of the other one of P-type silicon and N-type silicon.